Quad Transparent Latch

The MC14042B Quad Transparent Latch is constructed with MOS P-channel and N-channel enhancement mode devices in a single monolithic structure. Each latch has a separate data input, but all four latches share a common clock. The clock polarity (high or low) used to strobe data through the latches can be reversed using the polarity input. Information present at the data input is transferred to outputs Q and \overline{Q} during the clock level which is determined by the polarity input. When the polarity input is in the logic "0" state, data is transferred during the low clock level, and when the polarity input is in the logic "1" state the transfer occurs during the high clock level.

Features

- Buffered Data Inputs
- Common Clock
- Clock Polarity Control
- Q and Q Outputs
- Double Diode Input Protection
- Supply Voltage Range = 3.0 Vdc to 1 8 Vdc
- Capable of Driving Two Low-power TTL Loads or One Low-power Schottky TTL Load Over the Rated Temperature Range
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- This Device is Pb-Free and is RoHS Compliant

MAXIMUM RATINGS (Voltages Referenced to VSS)

Symbol	Parameter	Value	Unit
V _{DD}	DC Supply Voltage Range	-0.5 to +18.0	V
V _{in} , V _{out}	Input or Output Voltage Range (DC or Transient)	-0.5 to V _{DD} + 0.5	V
I _{in} , I _{out}	Input or Output Current (DC or Transient) per Pin	±10	mA
P _D	Power Dissipation, per Package (Note 1)	500	mW
T _A	Ambient Temperature Range	-55 to +125	°C
T _{stg}	Storage Temperature Range	-65 to +150	°C
TL	Lead Temperature (8–Second Soldering)	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Temperature Derating: "D/DW" Packages: -7.0 mW/°C From 65°C To 125°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range $V_{SS} \leq (V_{in} \text{ or } V_{out}) \leq V_{DD}$.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either V_{SS} or V_{DD}). Unused outputs must be left open.



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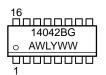


SOIC-16 D SUFFIX CASE 751B

PIN ASSIGNMENT

Q3		1 ●	16	þ	V_{DD}
Q0	d	2	15	þ	Q3
<u>Q</u> 0	d	3	14	þ	D3
D0	d	4	13	þ	D2
CLOCK		5	12	þ	Q2
POLARITY		6	11	þ	Q2
D1		7	10	þ	Q1
V_{SS}	þ	8	9	þ	Q1

MARKING DIAGRAM



A = Assembly Location
WL = Wafer Lot

YY, Y = Year

WW = Work Week

G = Pb-Free Indicator

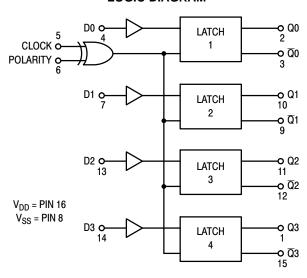
ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

TRUTH TABLE

Clock	Polarity	q
0	0	Data
1	0	Latch
1	1	Data
0	1	Latch

LOGIC DIAGRAM



ORDERING INFORMATION

Device	Package	Shipping [†]
MC14042BDG	SOIC-16 (Pb-Free)	48 Units / Rail
NLV14042BDG*	SOIC-16 (Pb-Free)	48 Units / Rail
MC14042BDR2G	SOIC-16 (Pb-Free)	2500 Units / Tape & Reel
NLV14042BDR2G*	SOIC-16 (Pb-Free)	2500 Units / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

ELECTRICAL CHARACTERISTICS (Voltages Referenced to V_{SS})

				-5	5°C		25°C		12	5°C	
Characteristic		Symbol	V _{DD} Vdc	Min	Max	Min	Typ (Note 2)	Max	Min	Max	Unit
Output Voltage V _{in} = V _{DD} or 0	"0" Level	V _{OL}	5.0 10 15	- - -	0.05 0.05 0.05	- - -	0 0 0	0.05 0.05 0.05	- - -	0.05 0.05 0.05	Vdc
V _{in} = 0 or V _{DD}	"1" Level	V _{OH}	5.0 10 15	4.95 9.95 14.95	- - -	4.95 9.95 14.95	5.0 10 15	- - -	4.95 9.95 14.95	- - -	Vdc
Input Voltage $(V_O = 4.5 \text{ or } 0.5 \text{ Vdc})$ $(V_O = 9.0 \text{ or } 1.0 \text{ Vdc})$ $(V_O = 13.5 \text{ or } 1.5 \text{ Vdc})$	"0" Level	V _{IL}	5.0 10 15	- - -	1.5 3.0 4.0	- - -	2.25 4.50 6.75	1.5 3.0 4.0	- - -	1.5 3.0 4.0	Vdc
$(V_O = 0.5 \text{ or } 4.5 \text{ Vdc})$ $(V_O = 1.0 \text{ or } 9.0 \text{ Vdc})$ $(V_O = 1.5 \text{ or } 13.5 \text{ Vdc})$	"1" Level	V _{IH}	5.0 10 15	3.5 7.0 11	- - -	3.5 7.0 11	2.75 5.50 8.25	- - -	3.5 7.0 11	- - -	Vdc
Output Drive Current $ \begin{aligned} &(V_{OH}=2.5 \text{ Vdc})\\ &(V_{OH}=4.6 \text{ Vdc})\\ &(V_{OH}=9.5 \text{ Vdc})\\ &(V_{OH}=13.5 \text{ Vdc}) \end{aligned} $	Source	IOH	5.0 5.0 10 15	-3.0 -0.64 -1.6 -4.2	- - -	-2.4 -0.51 -1.3 -3.4	-4.2 -0.88 -2.25 -8.8		-1.7 -0.36 -0.9 -2.4		mAdc
$(V_{OL} = 0.4 \text{ Vdc})$ $(V_{OL} = 0.5 \text{ Vdc})$ $(V_{OL} = 1.5 \text{ Vdc})$	Sink	I _{OL}	5.0 10 15	0.64 1.6 4.2	- - -	0.51 1.3 3.4	0.88 2.25 8.8	- - -	0.36 0.9 2.4	- - -	mAdc
Input Current		I _{in}	15	_	±0.1	-	±0.00001	±0.1	-	±1.0	μAdc
Input Capacitance (V _{in} = 0)		C _{in}	-	-	-	_	5.0	7.5	-	-	pF
Quiescent Current (Per Package)		I _{DD}	5.0 10 15	- - -	1.0 2.0 4.0	- - -	0.002 0.004 0.006	1.0 2.0 4.0	_ _ _	30 60 120	μAdc
Total Supply Current (Note (Dynamic plus Quiesce Per Package) (C _L = 50 pF on all output buffers switching)	lτ	5.0 10 15			$I_T = (2$	1.0 μΑ/kHz) f 2.0 μΑ/kHz) f 3.0 μΑ/kHz) f	+ I _{DD}		,	μAdc	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.

$$I_T(C_L) = I_T(50 \text{ pF}) + (C_L - 50) \text{ Vfk}$$

where: I_T is in μA (per package), C_L in pF, $V = (V_{DD} - V_{SS})$ in volts, f in kHz is input frequency, and k = 0.004.

^{3.} The formulas given are for the typical characteristics only at 25°C.
4. To calculate total supply current at loads other than 50 pF:

SWITCHING CHARACTERISTICS (Note 5) ($C_L = 50 \text{ pF}, T_A = 25^{\circ}C$)

Characteristic	Symbol	V _{DD}	Min	Typ (Note 6)	Max	Unit
Output Rise and Fall Time $t_{TLH}, t_{THL} = (1.5 \text{ ns/pF}) \text{ C}_L + 25 \text{ ns}$ $t_{TLH}, t_{THL} = (0.75 \text{ ns/pF}) \text{ C}_L + 12.5 \text{ ns}$ $t_{TLH}, t_{THL} = (0.55 \text{ ns/pF}) \text{ C}_L + 9.5 \text{ ns}$	t _{TLH} , t _{THL}	5.0 10 15	- - -	100 50 40	200 100 80	ns
Propagation Delay Time, D to Q, \overline{Q} t_{PLH} , t_{PHL} = (1.7 ns/pF) C_L + 135 ns t_{PLH} , t_{PHL} = (0.66 ns/pF) C_L + 57 ns t_{PLH} , t_{PHL} = (0.5 ns/pF) C_L + 35 ns	t _{PLH} , t _{PHL}	5.0 10 15	- - -	220 90 60	440 180 120	no
Propagation Delay Time, Clock to Q, \overline{Q} t _{PLH} , t _{PHL} = (1.7 ns/pF) C _L + 135 ns t _{PLH} , t _{PHL} = (0.66 ns/pF) C _L + 57 ns t _{PLH} , t _{PHL} = (0.5 ns/pF) C _L + 35 ns	t _{PLH} , t _{PHL}	5.0 10 15	- - -	220 90 60	440 180 120	ns
Clock Pulse Width	^t wH	5.0 10 15	300 100 80	150 50 40	- - -	ns
Clock Pulse Rise and Fall Time	t _{TLH} , t _{THL}	5.0 10 15	- - -	- - -	15 5.0 4.0	μs
Hold Time	t _h	5.0 10 15	100 50 40	50 25 20	- - -	ns
Setup Time	t _{su}	5.0 10 15	50 30 25	0 0 0	- - -	ns

^{5.} The formulas given are for the typical characteristics only at 25°C.
6. Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.

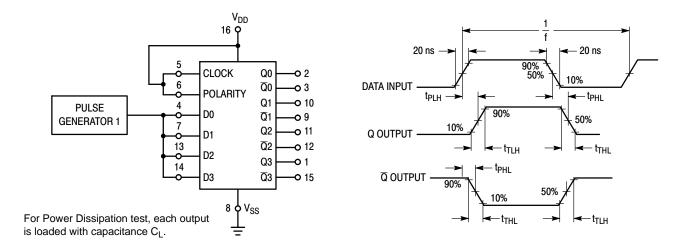
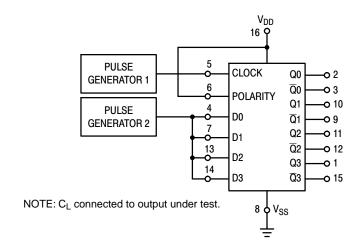
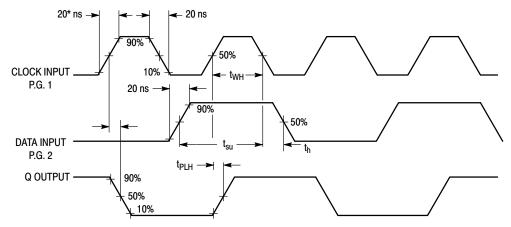


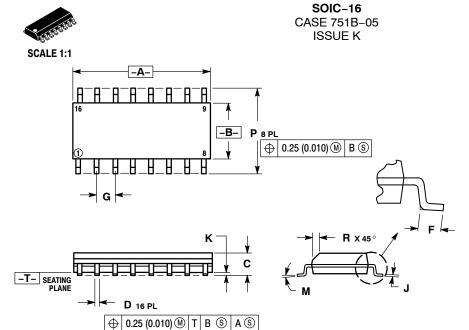
Figure 1. AC and Power Dissipation Test Circuit and Timing Diagram (Data to Output)





*Input clock rise time is 20 ns except for maximum rise time test.

Figure 2. AC Test Circuit and Timing Diagram (Clock to Output)



DATE 29 DEC 2006

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI
- THE NOTION AND TOLETANOING FER ANSI'Y 14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
- PHOI HUSION.

 MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.

 DIMENSION D DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR PROTRUSION

 SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D

 DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	9.80	10.00	0.386	0.393
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	BSC	0.050) BSC
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
Р	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

STYLE 1:		STYLE 2:		STYLE 3:		STYLE 4:			
	COLLECTOR		CATHODE	PIN 1.	COLLECTOR, DYE #1	PIN 1.	COLLECTOR, DY		
2.	BASE		ANODE	2.	BASE, #1	2.	COLLECTOR, #1		
3.	EMITTER	3.	NO CONNECTION	3.	EMITTER, #1	3.	COLLECTOR, #2		
4.	NO CONNECTION	4.	CATHODE	4.	COLLECTOR, #1	4.	COLLECTOR, #2		
5.	EMITTER	5.	CATHODE	5.	COLLECTOR, #2	5.	COLLECTOR, #3		
6.	BASE	6.	NO CONNECTION	6.	BASE, #2	6.	COLLECTOR, #3		
7.	COLLECTOR	7.	ANODE	7.	EMITTER, #2	7.	COLLECTOR, #4		
8.	COLLECTOR	8.	CATHODE	8.	COLLECTOR, #2	8.	COLLECTOR, #4		
9.	BASE		CATHODE	9.	COLLECTOR, #3	9.	BASE, #4		
10.	EMITTER		ANODE	10.	BASE, #3	10.	EMITTER, #4		
11.			NO CONNECTION	11.	EMITTER, #3	11.	BASE, #3		
12.	EMITTER		CATHODE	12.	COLLECTOR, #3	12.	EMITTER, #3		
13.	BASE		CATHODE	13.	COLLECTOR, #4	13.	BASE, #2	SOLDER	RING FOOTPRINT
14.			NO CONNECTION	14.	BASE, #4	14.	EMITTER, #2	SOLDER	IIIIG FOOTFRINT
15.	EMITTER			15.	EMITTER, #4	15.	BASE, #1		8X
16.	COLLECTOR	16.	CATHODE	16.	COLLECTOR, #4	16.	EMITTER, #1	4	— 6.40 — >
								-	0.10
STYLE 5:		STYLE 6:		STYLE 7:					16X 1.12 <
PIN 1.	DRAIN, DYE #1		CATHODE	PIN 1.	SOURCE N-CH				, 1 1
2.	DRAIN, #1		CATHODE	2.	COMMON DRAIN (OUTPUT	7)		. 🗀 1	16
3.	DRAIN, #2	3.	CATHODE	3.	COMMON DRAIN (OUTPUT			↓ — ·	
4.	DRAIN, #2	4.	CATHODE	4.	GATE P-CH	,			
5.	DRAIN, #3	5.	CATHODE	5.	COMMON DRAIN (OUTPUT	7)		16X	
6.	DRAIN, #3	6.	CATHODE	6.	COMMON DRAIN (OUTPUT			.58 J	' <u> </u>
7.	DRAIN, #4	7.	CATHODE	7.	COMMON DRAIN (OUTPUT		U	.50	ı —
8.	DRAIN, #4	8.	CATHODE	8.	SOURCE P-CH `	,			
9.	GATE, #4	9.	ANODE	9.	SOURCE P-CH				
10.	SOURCE, #4	10.	ANODE	10.	COMMON DRAIN (OUTPUT	7)			
11.	GATE, #3	11.	ANODE	11.	COMMON DRAIN (OUTPUT	ń			
12.	SOURCE, #3	12.	ANODE	12.	COMMON DRAIN (OUTPUT	ń			
13.	GATE, #2	13.	ANODE	13.	GATE N-CH	,			
14.	SOURCE, #2	14.	ANODE	14.	COMMON DRAIN (OUTPUT	7)			— ↓ PITCH
15.	GATE, #1	15.	ANODE	15.	COMMON DRAIN (OUTPUT				<u> </u>
16.	SOURCE, #1	16.	ANODE	16.	SOURCE N-CH				
	*							□ 8	9 + - + -
								— °	_ ↑
									DIMENSIONS: MILLIMETERS
									DIMENSIONS: MILLIMETERS

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